

ABSTRACT

Disclosed are a staircase structure, a method for manufacturing the same, and a semiconductor structure. The staircase structure includes: a plurality of conductive layers spaced apart along a first direction, where each conductive layer includes at least two sub-conductive layers spaced apart along a second direction, and the conductive layer extends along a third direction; and a plurality of step structures spaced apart along the second direction, one column of the sub-conductive layers spaced apart along the first direction being in contact connection with at least one step structure, where each step structure includes a plurality of conductive pillars electrically insulated from each other, one conductive pillar is in contact connection with one sub-conductive layer, and the conductive pillar in contact connection with the one sub-conductive layer is electrically insulated from the other sub-conductive layers; and in a column of the conductive layers spaced apart along the first direction, the conductive layers are in contact connection with the conductive pillars in a one-to-one manner. Embodiments of the present disclosure are at least beneficial to reducing the overall horizontal area occupied by the staircase structure and improving the integration density of the conductive pillars in the staircase structure.

[FIG. 1]